

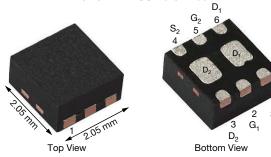
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Vishay Siliconix

Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)						
	0.054 at V _{GS} = -4.5 V	-4.5 ^a							
-20	0.070 at V _{GS} = -2.5 V	-4.5 ^a	9.5 nC						
-20	0.104 at V _{GS} = -1.8 V	-4.5 ^a							
	0.165 at V _{GS} = -1.5 V	-1.5							

PowerPAK® SC-70-6L Dual



Marking Code: DP Ordering Information:

SiA923AEDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2500 V
- 100 % R_q Tested

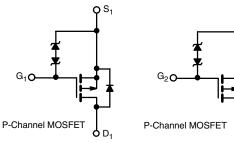
 Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



COMPLIANT HALOGEN FREE

APPLICATIONS

- Charger Switches and Load Switches for Portable Devices
- DC/DC Converters



PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	-20	V		
Gate-Source Voltage		V _{GS}	± 8	v		
	T _C = 25 °C		-4.5 ^a			
Continuous Drain Current (T. 150 °C)	T _C = 70 °C		-4.5 ^a			
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	-4.5 a,b,c			
	T _A = 70 °C		-4.5 a,b,c	Α		
Pulsed Drain Current (t = 100 μs)		I _{DM}				
0 " 0 5 " 5" 1 0 1	T _C = 25 °C		-4.5 ^a			
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S —	-1.6 ^{b,c}			
	T _C = 25 °C		7.8			
Marian and Dissipation	T _C = 70 °C		5	14/		
Maximum Power Dissipation	T _A = 25 °C	P _D	1.9 ^{b,c}	W		
	T _A = 70 °C		1.2 b,c			
Operating Junction and Storage Temperature F	Range	T _J , T _{stg}	-55 to 150	**		
Soldering Recommendations (Peak Temperatur	re) d,e	j j	260	- °C		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum Junction-to-Ambient b,f	t ≤ 5 s	R _{thJA}	52	65	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16	C/VV				

Notes

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.



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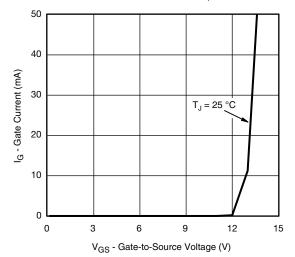
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	_	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$		-	-15	-	mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	2.5	-	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-	-0.9	V
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	-	± 0.3	± 3	μΑ
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	_	± 3	± 30	
	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	-	-	-1	
Zero Gate Voltage Drain Current		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	
On-State Drain Current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-15	-	-	Α
	(* /	V _{GS} = -4.5 V, I _D = -3.8 A	-	0.044	0.054	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -3.3 \text{ A}$	-	0.057	0.070	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -1 A	-	0.075	0.104	
		V _{GS} = -1.5 V, I _D = -0.5 A	0.097	0.165		
Forward Transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -3.8 \text{ A}$	-	11	-	S
Dynamic ^b				•	l	
Input Capacitance	C _{iss}		-	770	-	
Output Capacitance	C _{oss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	-	90	-	pF
Reverse Transfer Capacitance	C _{rss}		-	81	-	
Tabal Oaks Observe	0	V _{DS} = -10 V, V _{GS} = -8 V, I _D = -4.9 A	-	16.3	25	nC
Total Gate Charge	Q_g		-	9.5	14.5	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.9 \text{ A}$	-	1.4	-	
Gate-Drain Charge	Q_{gd}		-	2.3	-	
Gate Resistance	e Resistance R _g		1	5.1	10	Ω
Turn-On Delay Time	t _{d(on)}		-	15	25	
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_1 = 2.6 \Omega$	-	16	25	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.9 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	30	45	
Fall Time	t _f	f		10	15	
Turn-On Delay Time	t _{d(on)}		-	7	15	ns
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_1 = 2.6 \Omega$	-	12	20	
Turn-Off Delay Time	t _{d(off)}	1 00 A V		26	40	1
Fall Time	t _f		-	10	15	
Drain-Source Body Diode Characterist	ics			•		
Continuous Source-Drain Diode Current	Is	T _C = 25 °C	-	-	-4.5	۸
Pulse Diode Forward Current I _{SM}			-	-	-15	A
Body Diode Voltage	V_{SD}	I _S = -3.9 A, V _{GS} = 0 V	-	-0.9	-1.2	V
Body Diode Reverse Recovery Time t _{rr}			-	13	25	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 20 A dl/dt 100 A/: T 05 00	-	5.5	12	nC
Reverse Recovery Fall Time	ta	$I_F = -3.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	7.5	-	ns
Reverse Recovery Rise Time	t _b		-	5.5	_	

Notes

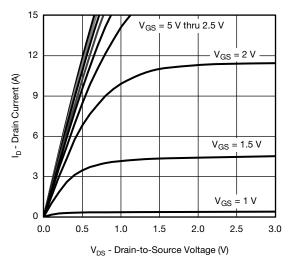
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

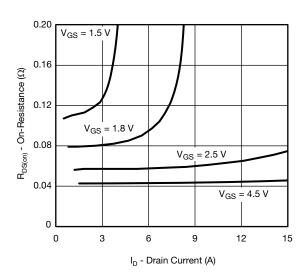




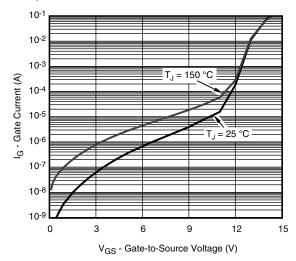
Gate Current vs. Gate-to-Source Voltage



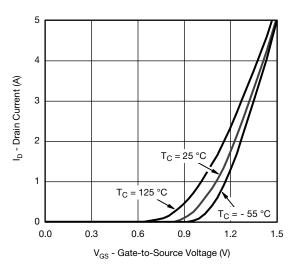
Output Characteristics



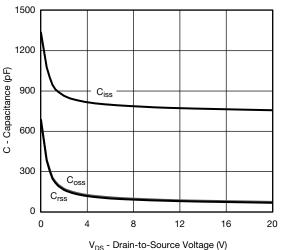
On-Resistance vs. Drain Current and Gate Voltage



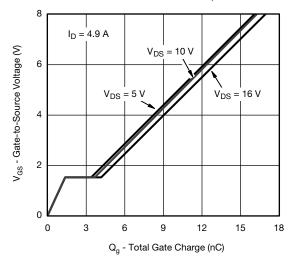
Gate Current vs. Gate-to-Source Voltage



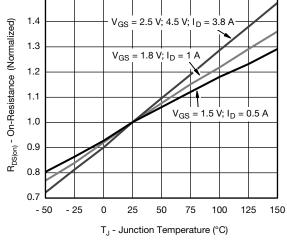
Transfer Characteristics



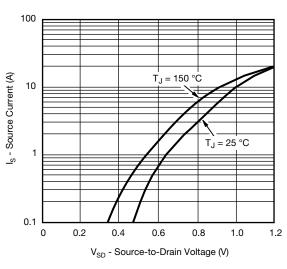




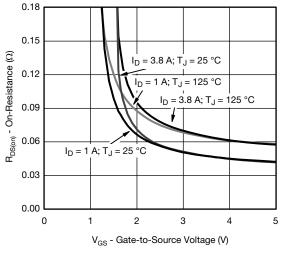
Gate Charge



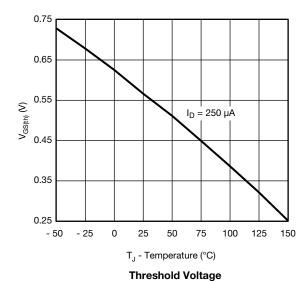
On-Resistance vs. Junction Temperature



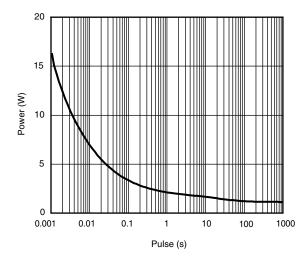
Source-Drain Diode Forward Voltage



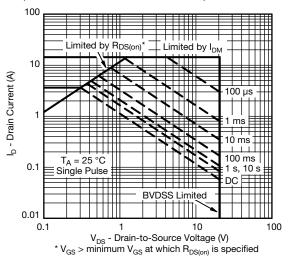
On-Resistance vs. Gate-to-Source Voltage



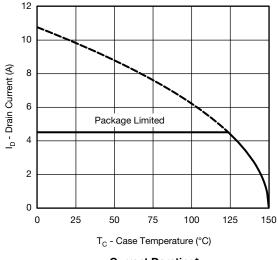
Single Pulse Power, Junction-to-Ambient

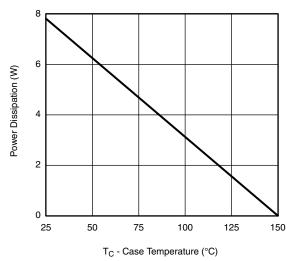






Safe Operating Area, Junction-to-Ambient



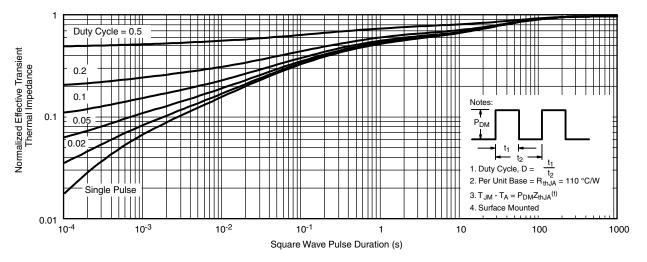


Current Derating*

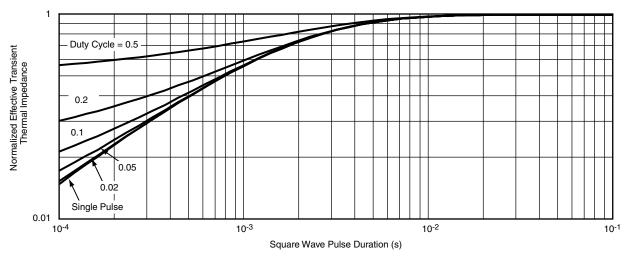
Power Derating

^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

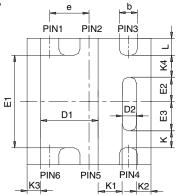
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262936.





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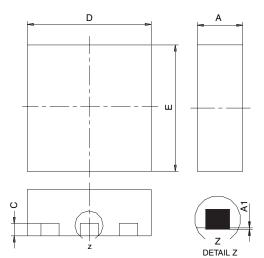
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

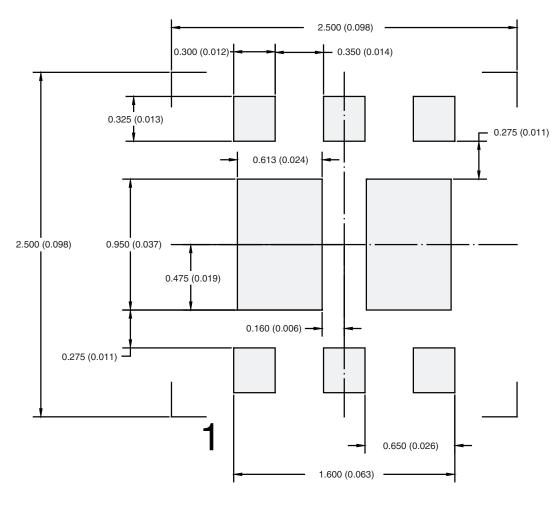
	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	1		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP 0.010 TYP			1					
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	1	0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 - Rev. C. 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Revision: 02-Oct-12 Document Number: 91000

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SIA923AEDJ-T1-GE3